

**In the Claims**

Claims 1-107 (cancelled).

Claim 108 (currently amended): A capacitor construction, comprising:

an electrically insulative material;

a region extending into the material, the electrically insulative material comprising a periphery around the region;

agglomerates along the periphery; the agglomerates comprising one or more noble metals, the agglomerates including spaced islands which are in direct physical contact with the electrically insulative material;

a first conductive layer within the region and extending over agglomerates;

a dielectric layer over the first conductive layer; and

a second conductive layer over the dielectric layer; the second conductive layer being capacitively coupled with the first conductive layer.

Claim 109 (original): The capacitor construction of claim 108 wherein the insulative material comprises borophosphosilicate glass.

Claim 110 (original): The capacitor construction of claim 108 wherein the insulative material comprises phosphosilicate glass.

Claim 111 (currently amended): ~~The capacitor construction of claim 108~~ A capacitor construction, comprising:

an electrically insulative material;

a region extending into the material, the material comprising a periphery around the region;

agglomerates along the periphery; the agglomerates comprising one or more noble metals;

a first conductive layer within the region and extending over agglomerates;

a dielectric layer over the first conductive layer;

a second conductive layer over the dielectric layer; the second conductive layer being capacitively coupled with the first conductive layer; and

wherein the insulative material comprises borophosphosilicate glass having one or both of silicon dioxide and aluminum oxide thereover.

Claim 112 (currently amended): ~~The capacitor construction of claim 108 further comprising~~

A capacitor construction, comprising:

an electrically insulative material;

a region extending into the material, the material comprising a periphery around the region;

agglomerates along the periphery; the agglomerates comprising one or more noble metals;

a first conductive layer within the region and extending over agglomerates;

a dielectric layer over the first conductive layer;

a second conductive layer over the dielectric layer; the second conductive layer being capacitively coupled with the first conductive layer;

cavities extending into the periphery between the agglomerates[[,]] ; and

wherein the first conductive layer extends into the cavities.

Claim 113 (original): The capacitor construction of claim 108 wherein the one or more noble metals are selected from the group consisting of Pt, Rh, Ru, Pd and Ir.

Claim 114 (original): The capacitor construction of claim 108 wherein the agglomerates consist essentially of the one or more noble metals.

Claim 115 (original): The capacitor construction of claim 108 wherein the agglomerates consist essentially of Pt.

Claim 116 (original): The capacitor construction of claim 108 incorporated into a DRAM array.